Voltage Regulator - Low Noise, Low Dropout

150 mA

The NCP4586 is a CMOS 150 mA low dropout linear with low noise, high ripple rejection, low dropout, high output voltage accuracy and low supply current. The device is available in three configurations: enable high, enable low and enable high plus auto-discharge. Small packages allow mounting on high density PCBs. This is an excellent general purpose regulator, well suited to many applications.

Features

- Operating Input Voltage Range: 1.7 V to 6.5 V
- Output Voltage Range: 1.2 to 5.0 V (available in 0.1 V steps)
- Very Low Dropout: 320 mV Typ. at 150 mA
- $\pm 1\%$ Output Voltage Accuracy (V_{OUT} > 2 V, T_J = 25°C)
- High PSRR: 80 dB at 1 kHz
- Current Fold Back Protection
- Stable with a 0.47 μF Ceramic Capacitors
- Available in 1.0 x 1.0 UDFN, SC-82AB and SOT23-5 Package
- These are Pb-Free Devices

Typical Applications

- Battery Powered Equipment
- Portable Communication Equipment
- Cameras, MP3 Players and Camcorder
- High Stability Voltage Reference

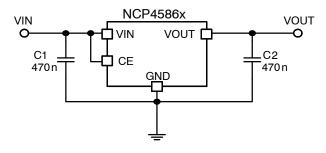


Figure 1. Typical Application Schematic



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MARKING DIAGRAMS













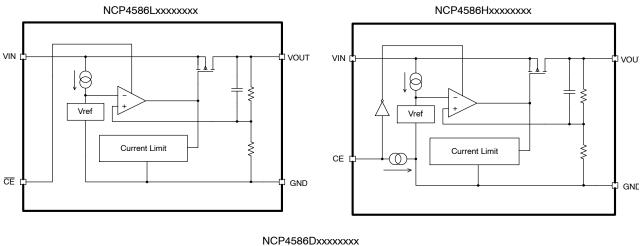
SOT-23-5 CASE 1212



XX, XXX= Specific Product Code MM = Lot Number

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 15 of this data sheet.



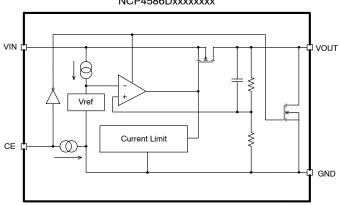


Figure 2. Simplified Schematic Block Diagram

PIN FUNCTION DESCRIPTION

Pin No. UDFN4	Pin No. SC82-AB	Pin No. SOT23-5	Pin Name	Description
4	4	1	VIN	Input pin
2	2	2	GND	Ground
3	1	3	CE/CE	Chip enable pin ("L" active / "H" active)
1	3	5	VOUT	Output pin
_	-	4	NC	No connection

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input Voltage (Note 1)	V _{IN}	7	V
Output Voltage	Vout	-0.3 to VIN + 0.3	V
Chip Enable Input	Vce	-0.3 to 7	V
Output Current	l _{out}	200	mA
Power Dissipation UDFN4	P _D	400	
Power Dissipation SC-82AB		380	mW
Power Dissipation SOT23-5		420	
Maximum Junction Temperature	$T_{J(MAX)}$	+150	°C
Operating Ambient Temperature	T _A	-40 to +85	°C
Storage Temperature	T _{STG}	-55 to +125	°C
ESD Capability, Human Body Model (Note 2)	ESD _{HBM}	2000	V
ESD Capability, Machine Model (Note 2)	ESD _{MM}	200	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Refer to ELECTRICAL CHARACTERISTIS and APPLICATION INFORMATION for Safe Operating Area.

- 2. This device series incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per AEC-Q100-002 (EIA/JESD22-A114) ESD Machine Model tested per AEC-Q100-003 (EIA/JESD22-A115) Latchup Current Maximum Rating tested per JEDEC standard: JESD78.

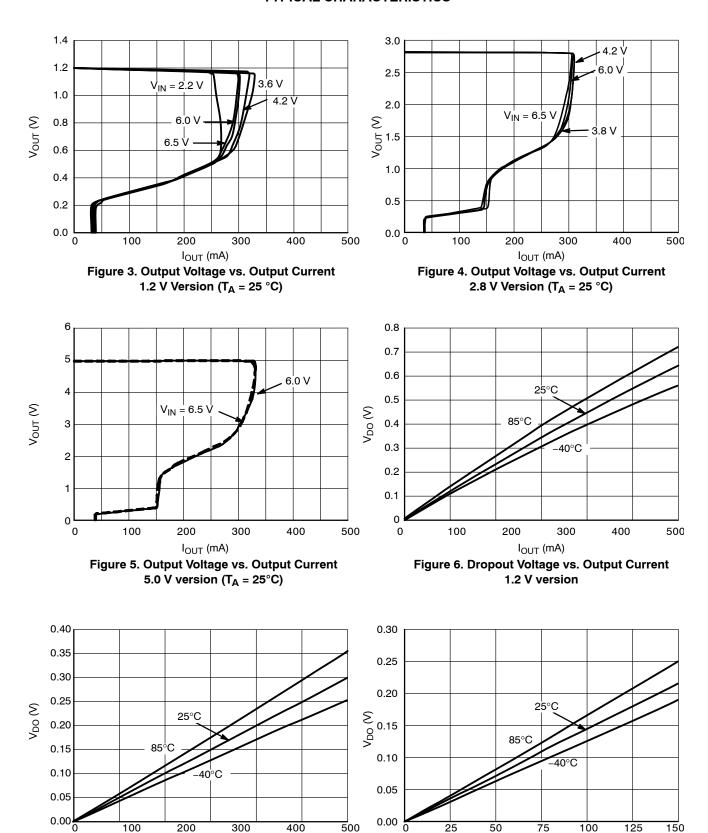
THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Characteristics, UDFN4 Thermal Resistance, Junction-to-Air	$R_{ hetaJA}$	250	°C/W
Thermal Characteristics, SOT23-5 Thermal Resistance, Junction-to-Air	$R_{ heta JA}$	238	°C/W
Thermal Characteristics, SC 82AB Thermal Resistance, Junction–to–Air	$R_{ heta JA}$	263	°C/W

ELECTRICAL CHARACTERISTICS $-40^{\circ}\text{C} \le T_A \le 85^{\circ}\text{C}$; $V_{\text{IN}} = V_{\text{OUT}(\text{NOM})} + 1 \text{ V or } 2.5 \text{ V}$, whichever is greater; $I_{\text{OUT}} = 1 \text{ mA}$, $C_{\text{IN}} = C_{\text{OUT}} = 0.47 \,\mu\text{F}$, unless otherwise noted. Typical values are at $T_A = +25 \,^{\circ}\text{C}$.

Parameter	Test Conditions		Symbol	Min	Тур	Max	Unit
Operating Input Voltage			Vin	1.7		6.5	V
Output Voltage	TA = +25 °C	V _{OUT} > 2 V	Vout	x0.99		x1.01	V
		V _{OUT} ≤ 2 V	1	-20		20	mV
	-40°C ≤ Ta ≤ 85°C	V _{OUT} > 2 V	1	x0.985		x1.015	V
		V _{OUT} ≤ 2 V	1	-30		30	mV
Output Voltage Temp. Coefficient	$T_A = -4$	10 to 85°C			±20		ppm/°C
Line Regulation	V _{IN} = Vout	+ 0.5 V to 5 V	Line _{Reg}		0.02	0.10	%/V
Load Regulation	Iout = 1 m	nA to 150 mA	Load _{Reg}		10	30	mV
Dropout Voltage	I _{OUT} = 150 mA	1.2 V ≤ V _{OUT} < 1.5 V	VDO		0.67	1.00	V
		1.5 V ≤ V _{OUT} < 1.7 V	1		0.54	0.81	1
		1.7 V ≤ V _{OUT} < 2.0 V	1		0.46	0.68	1
		2.0 V ≤ V _{OUT} < 2.5 V	1		0.41	0.60	1
		2.5 V ≤ V _{OUT} < 4.0 V	1		0.32	0.51	1
		4.0 V ≤ V _{OUT}	1		0.24	0.37	1
Output Current		•	Іоит	150			mA
Short Current Limit	V _{OU}	T = 0 V	I _{SC}		40		mA
Quiescent Current	Іоит	= 0 mA	IQ		38	58	μΑ
Standby Current	V _{CE} = V _{IN} (L version	on), V _{CE} = 0 V(H and n), T _A = 25°C	ISTB		0.1	1	μΑ
CE/CE Pin Threshold Voltage	CE / CE Inp	out Voltage "H"	VCEH	1.0			V
	CE / CE Inp	out Voltage "L"	VCEL			0.4	1
CE Pull Down Current	H and	D version	IPD		0.4		μΑ
Power Supply Rejection Ratio	VIN = V _{OUT} + 1 V or 3.0 V whichever is higher, IOUT = 30 mA, f = 1 kHz		PSRR		80		dB
Output Noise Voltage	V _{OUT} = 1.2 V, I _{OUT} = 30 mA, f = 10 Hz to 100 kHz		Vn		30		μV _{rms}
Low Output N-ch Tr. On Resistance	D Version only, \	/ _{IN} = 4 V, V _{CE} = 0 V	R _{LOW}		30		Ω

TYPICAL CHARACTERISTICS



I_{OUT} (mA)

Figure 7. Dropout Voltage vs. Output Current

2.8 V Version

I_{OUT} (mA)

Figure 8. Dropout Voltage vs. Output Current

5.0 V Version

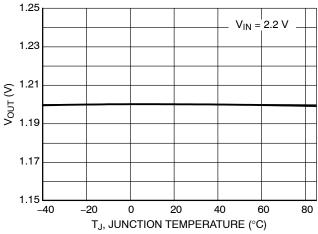


Figure 9. Output Voltage vs. Temperature, 1.2 V Version

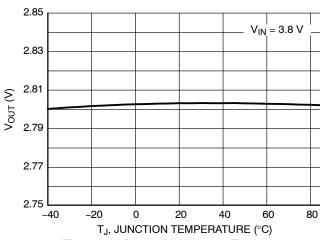


Figure 10. Output Voltage vs. Temperature, 2.8 V version

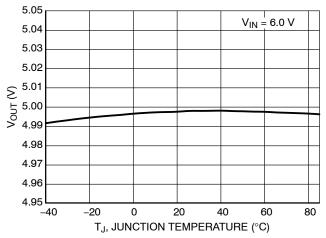


Figure 11. Output Voltage vs. Temperature, 5.0 V Version

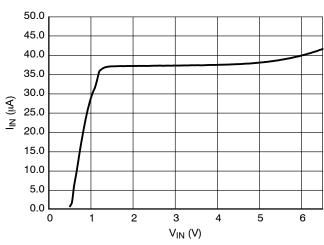


Figure 12. Supply Current vs. Input Voltage, 1.2 V Version

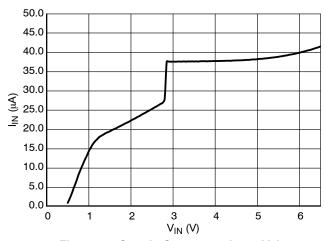


Figure 14. Supply Current vs. Input Voltage, 2.8 V Version

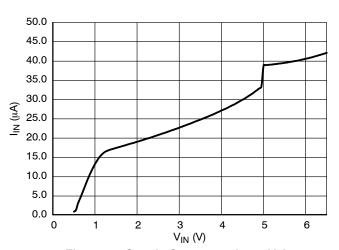


Figure 13. Supply Current vs. Input Voltage, 5.0 V version

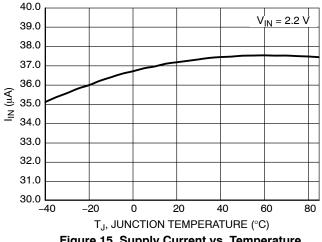


Figure 15. Supply Current vs. Temperature, 1.2 V Version

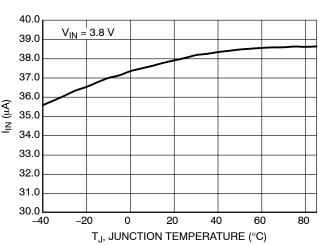


Figure 16. Supply Current vs. Temperature, 2.8 V Version

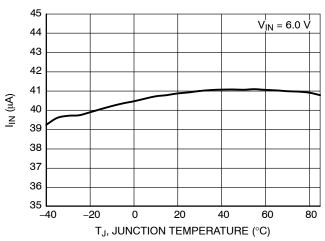


Figure 17. Supply Current vs. Temperature, 5.0 V Version

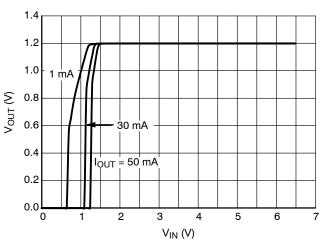


Figure 18. Output Voltage vs. Input Voltage, 1.2 V Version

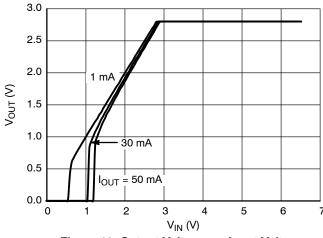


Figure 19. Output Voltage vs. Input Voltage, 2.8 V Version

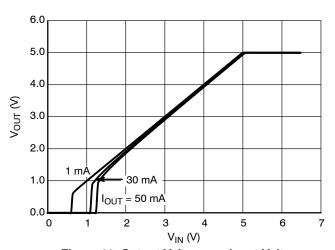
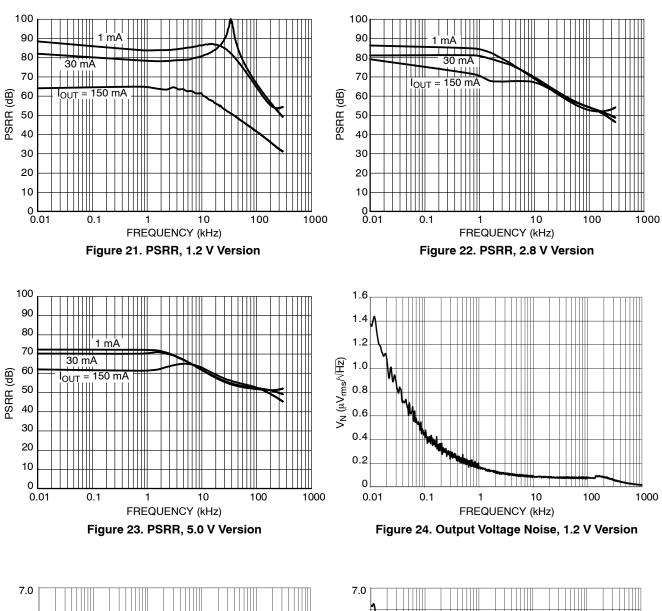
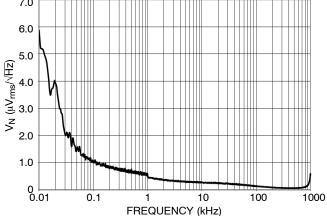


Figure 20. Output Voltage vs. Input Voltage, 5.0 V Version







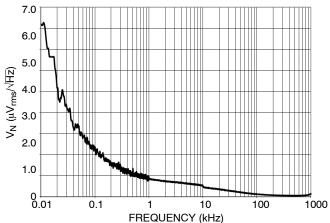


Figure 26. Output Voltage Noise, 5.0 V Version

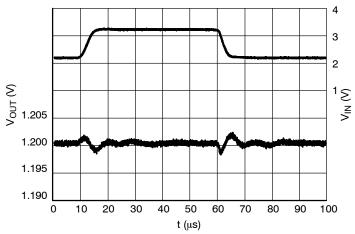


Figure 27. Line Transients, 1.2 V Version, $t_R = t_F = 5 \mu s$, $l_{OUT} = 30 \text{ mA}$

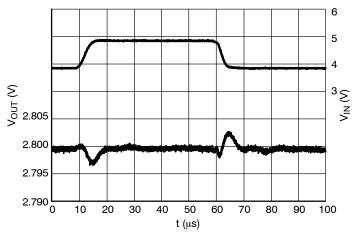


Figure 28. Line Transients, 2.8 V Version, $t_R \ = \ t_F \ = \ 5 \ \mu s, \ I_{OUT} \ = \ 30 \ mA$

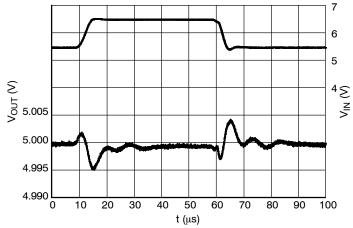


Figure 29. Line Transients, 5.0 V Version, $t_R = t_F = 5 \mu s$, $I_{OUT} = 30 \text{ mA}$

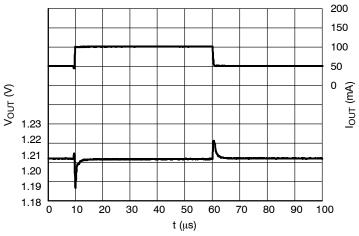


Figure 30. Load Transients, 1.2 V Version, $I_{OUT}=50-100$ mA, $t_R=t_F=0.5$ $\mu s,\ V_{IN}=2.2$ V

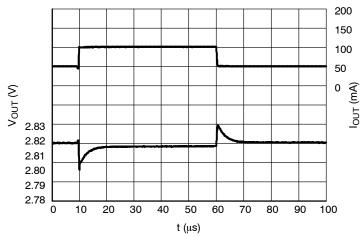


Figure 31. Load Transients, 2.8 V Version, I_{OUT} = 50 - 100 mA, t_R = t_F = 0.5 $\mu s,\,V_{IN}$ = 3.8 V

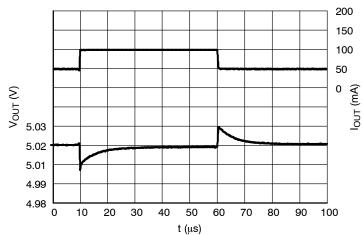


Figure 32. Load Transients, 5.0 V Version, I_{OUT} = 50 - 100 mA, t_R = t_F = 0.5 $\mu s,\,V_{IN}$ = 6.0 V

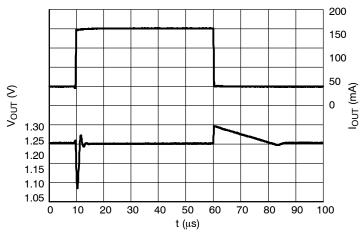


Figure 33. Load Transients, 1.2 V Version, I_{OUT} = 1 - 150 mA, t_R = t_F = 0.5 $\mu s, \, V_{IN}$ = 2.2 V

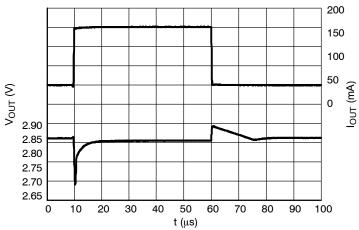


Figure 34. Load Transients, 2.8 V Version, I_{OUT} = 1 - 150 mA, t_R = t_F = 0.5 $\mu s, \, V_{IN}$ = 3.8 V

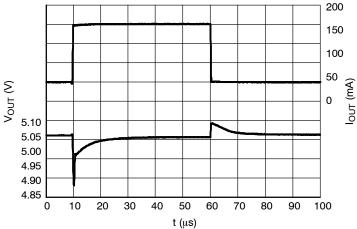


Figure 35. Load Transients, 5.0 V Version, I_{OUT} = 1 - 150 mA, t_R = t_F = 0.5 $\mu s, \, V_{IN}$ = 6.0 V

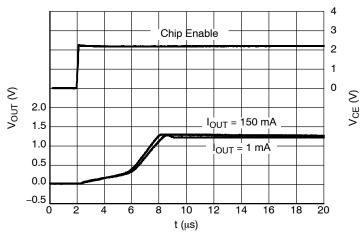


Figure 36. Start-up, 1.2 V Version, V_{IN} = 2.2 V

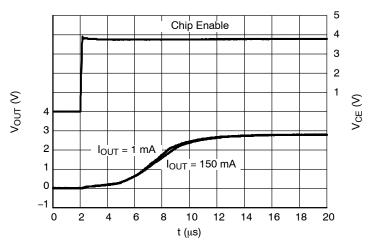
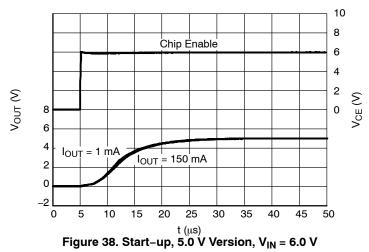


Figure 37. Start-up, 2.8 V Version, V_{IN} = 3.8 V



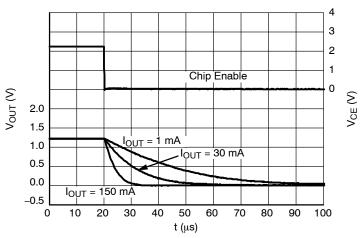


Figure 39. Shutdown, 1.2 V Version D, $V_{\text{IN}} = 2.2 \text{ V} \label{eq:VIN}$

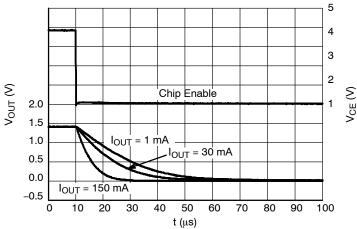


Figure 40. Shutdown, 2.8 V Version D, V_{IN} = 3.8 V

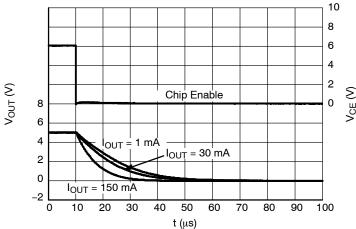


Figure 41. Shutdown, 5.0 V version D, V_{IN} = 6.0 V

APPLICATION INFORMATION

A typical application circuit for NCP4586 series is shown in Figure 42.

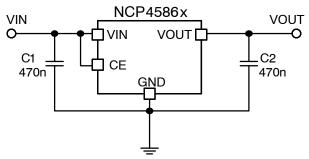


Figure 42. Typical Application Schematic

Input Decoupling Capacitor (C1)

A 470 nF ceramic input decoupling capacitor should be connected as close as possible to the input and ground pin of the NCP4586. Higher values and lower ESR improves line transient response.

Output Decoupling Capacitor (C2)

A 470 nF or larger ceramic output decoupling capacitor is sufficient to achieve stable operation of the IC. If a tantalum capacitor is used, and its ESR is high, loop oscillation may result. The capacitors should be connected as close as possible to the output and ground pins. Larger values and lower ESR improves dynamic parameters.

Enable Operation

The Enable pin $\overline{\text{CE}}$ or CE may be used for turning the regulator on and off. Control polarity is dependent on

version of IC. Active high or low versions are available; please see the ordering information table. The Enable pin has an internal pull down current source for versions H and D. If the enable function is not needed connect the $\overline{\text{CE}}$ pin to ground for version L or connect the CE pin to VIN for versions H and D.

Output Discharger

The D version includes a transistor between VOUT and GND that is used for faster discharging of the output capacitor. This function is activated when the IC goes into disable mode.

Thermal

As power across the IC increases, it might become necessary to provide some thermal relief. The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and also the ambient temperature affect the rate of temperature rise for the part. That is to say, when the device has good thermal conductivity through the PCB, the junction temperature will be relatively low with high power dissipation applications.

PCB Layout

Make VIN and GND line sufficient. If their impedance is high, noise pickup or unstable operation may result. Connect capacitors C1 and C2 as close as possible to the IC, and make wiring as short as possible.

ORDERING INFORMATION

Device	Nominal Output Voltage	Description	Marking	Package	Shipping [†]
NCP4586DSQ12T1G	1.2 V		LA		
NCP4586DSQ18T1G	1.8 V		LG		
NCP4586DSQ28T1G	2.8 V		MH	SC82AB	0000 / Table 0 Dead
NCP4586DSQ30T1G	3.0 V		NA	(Pb-Free)	3000 / Tape & Reel
NCP4586DSQ33T1G	3.3 V		ND		
NCP4586DSQ50T1G	5.0 V		QA		
NCP4586DMU12TCG	1.2 V	- - -	VA		
NCP4586DMU14TCG	1.4 V		VC		
NCP4586DMU15TCG	1.5 V		VD		
NCP4586DMU18TCG	1.8 V		VG		
NCP4586DMU25TCG	2.5 V	Enable High, Auto discharge	VQ	UDFN4 (Pb-Free)	10000 / Tape & Reel
NCP4586DMU28TCG	2.8 V	7 tate also::a.ge	VT	(. 2	
NCP4586DMU30TCG	3.0 V		VW		
NCP4586DMU33TCG	3.3 V		VZ		
NCP4586DMU50TCG	5.0 V		WS		
NCP4586DSN12T1G	1.2 V		H2A		
NCP4586DSN18T1G	1.8 V		H2G		
NCP4586DSN28T1G	2.8 V		H2T	SOT-23-5	0000 (Table 0.D.)
NCP4586DSN30T1G	3.0 V		H2W	(Pb-Free)	3000 / Tape & Reel
NCP4586DSN33T1G	3.3 V		H2Z	1	
NCP4586DSN50T1G	5.0 V		J2S	1	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NOTE: To order other package and voltage variants, please contact your ON Semiconductor sales representative.

MECHANICAL CASE OUTLINE

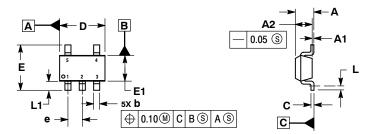
PACKAGE DIMENSIONS



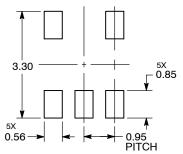


SOT-23 5-LEAD CASE 1212-01 **ISSUE A**

DATE 28 JAN 2011



RECOMMENDED **SOLDERING FOOTPRINT***



DIMENSIONS: MILLIMETERS

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSIONS: MILLIMETERS.
 3. DATUM C IS THE SEATING PLANE.

	MILLIMETERS				
DIM	MIN MAX				
Α		1.45			
A1	0.00	0.10			
A2	1.00	1.30			
b	0.30	0.50			
С	0.10	0.25			
D	2.70	3.10			
Е	2.50	3.10			
E1	1.50 1.80				
е	0.95 BSC				
L	0.20				
L1	0.45	0.75			

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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	DESCRIPTION:	SOT-23 5-LEAD		PAGE 1 OF 1

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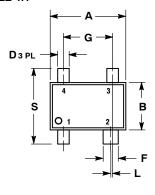
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

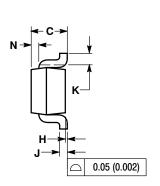


SC-82AB CASE 419C-02 ISSUE F

DATE 22 JUN 2012

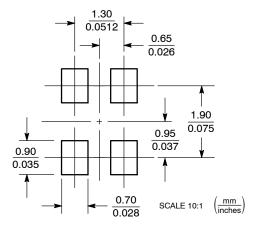
SCALE 4:1







SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. 419C-01 OBSOLETE. NEW STANDARD IS 419C-02.

 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE RI IRRS.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	1.80	2.20	0.071	0.087	
В	1.15	1.35	0.045	0.053	
С	0.80	1.10	0.031	0.043	
D	0.20	0.40	0.008	0.016	
F	0.30	0.50	0.012	0.020	
G	1.10	1.50	0.043	0.059	
Н	0.00	0.10	0.000	0.004	
J	0.10	0.26	0.004	0.010	
K	0.10		0.004		
L	0.05	0.05 BSC		0.002 BSC	
N	0.20	REF	0.008	REF	
S	1.80	2.40	0.07	0.09	

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Month Code Μ

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	SC-82AB		PAGE 1 OF 1	

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MECHANICAL CASE OUTLINE



UDFN4 1.0x1.0, 0.65P CASE 517BR-01 **ISSUE O**

DATE 27 OCT 2010

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION 6 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND
- 0.20 mm FROM TERMINAL.

4. COPLANARITY APPLIES TO THE EXPOSED
PAD AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	-	0.60		
A1	0.00	0.05		
A3	0.10	REF		
b	0.20	0.30		
D	1.00	BSC		
D2	0.43	0.53		
E	1.00	BSC		
е	0.65	BSC		
L	0.20	0.30		
L2	0.27	0.37		
L3	0.02	0.12		

GENERIC MARKING DIAGRAM*



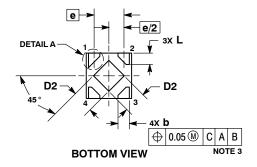
XX = Specific Device Code

MM = Date Code

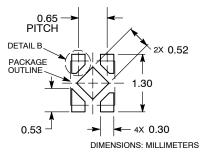
*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

4X L3 В c 0.18 PIN ONE REFERENCE **DETAIL A** 0.05 2X 🗀 0.05 С ¥ 0.23 3X 0.43 TOP VIEW (A3)0.05 C **≪** 3X 0 10 0.05 C **DETAIL B** C SEATING PLANE NOTE 4 SIDE VIEW



RECOMMENDED **MOUNTING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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